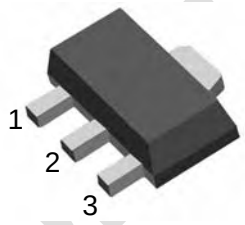
BF620 TRANSISTOR (NPN)

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

Power dissipation

$P_{CM:}$ 500 mW (Tamb=25℃)

Collector current

$I_{CM:}$ 50 mA

Collector-base voltage

$V_{(BR)CBO}$: 300 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=200V, I_E=0			10	nA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			50	nA
DC current gain	$h_{FE(1)}$	V_{CE}=20V, I_C=25mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=30mA, I_B=5mA			0.6	V
Transition frequency	f_T	V_{CE}=10V, I_C=100mA, f=100MHz	60			MHz

Marking	**DC**